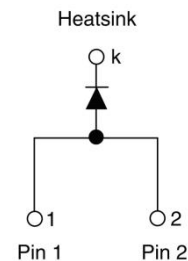


ESTF10SS60SD

Features

- Hyperfast recovery time
- Low Qrr and soft recovery
- Ideal for automated placement
- Glass passivated pellet chip junction
- Low forward voltage drop
- Low leakage current
- High forward surge capability



Applications

- Switching Power Supplies
- Snubber diode
- UPS
- Antiparalle Diode for high frequency Switching Devices

Absolute Maximum Ratings (Tc=25℃,otherwise specified)

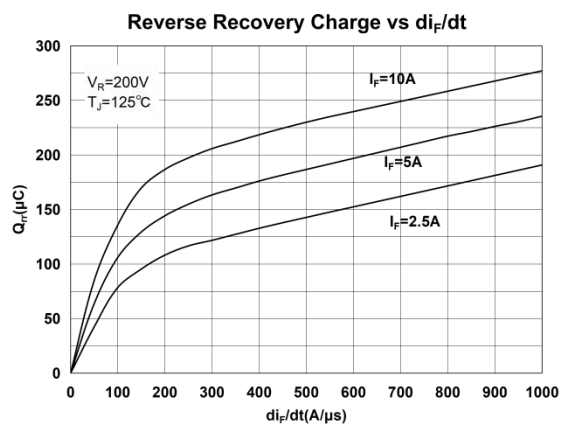
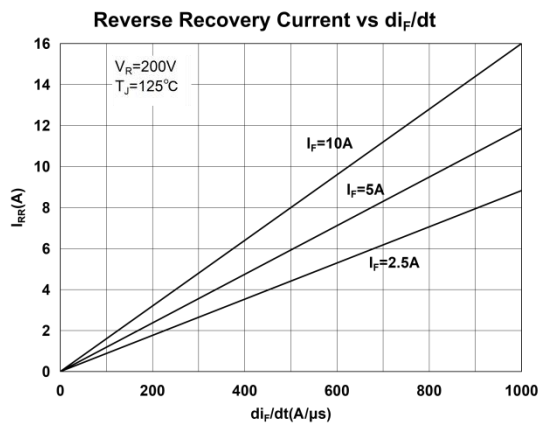
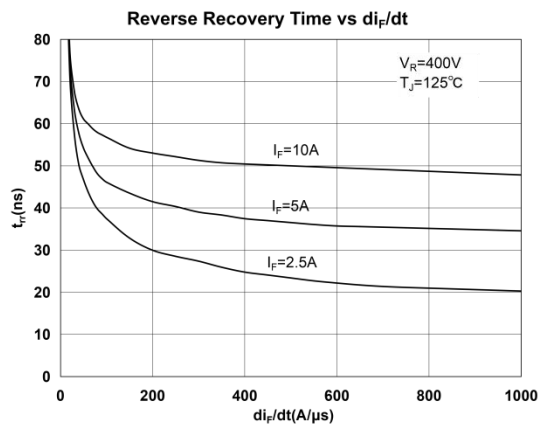
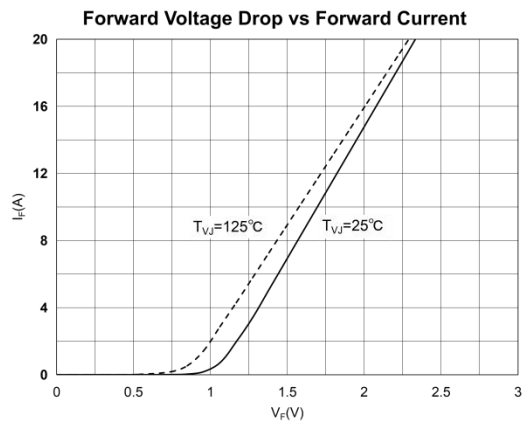
Symbol	Parameter	ratings	Unit
V_{RRM}	Repetitive peak reverse voltage @250μA	600	V
$I_{F(AV)}$	Average forward current	20	A
	Average forward current @Tc=100℃	10	A
I_{FSM}	Peak one Cycle Surge Forward @t=10ms	120	A
T_J	Junction Temperature	-55~+150	℃
T_{STG}	Storage temperature range	-55~+150	℃

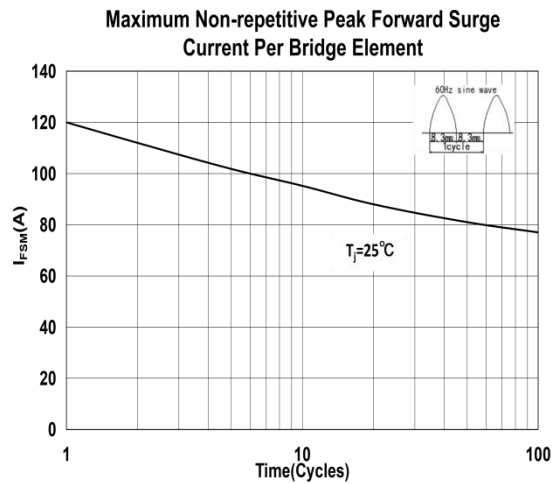
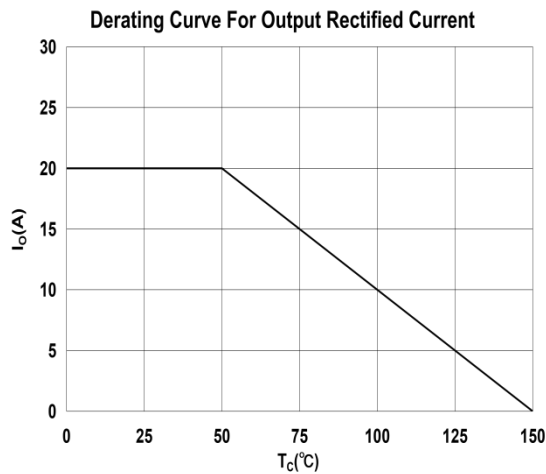
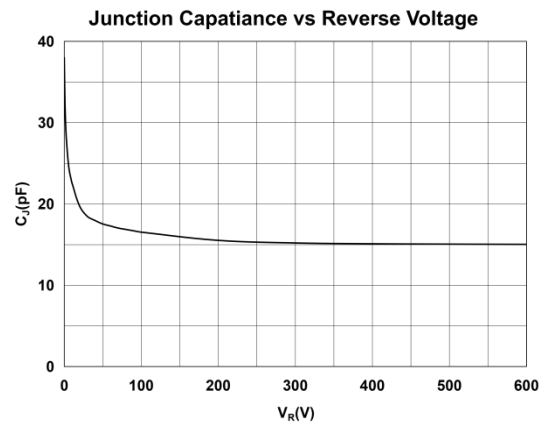
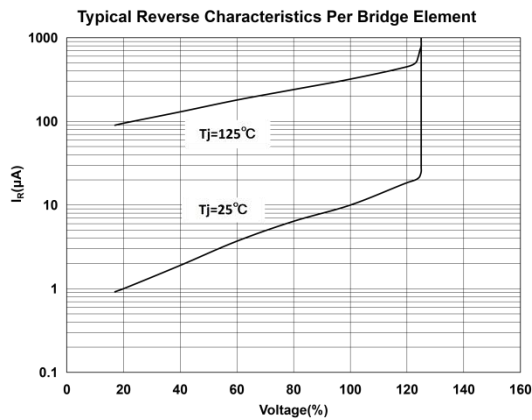
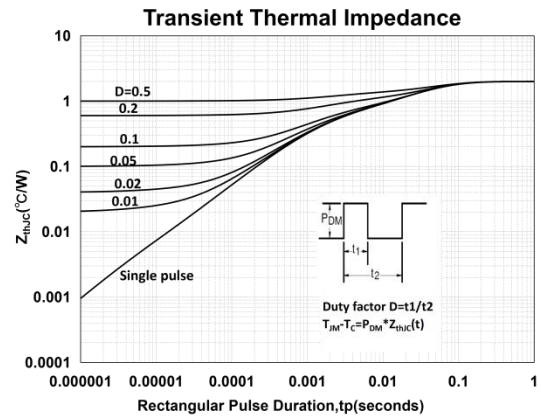
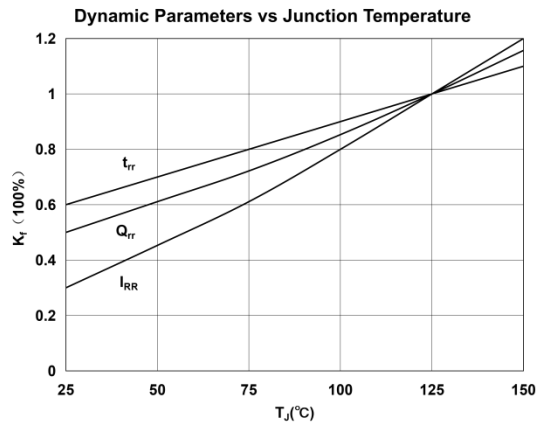
Electrical Characteristics (Tc=25℃,otherwise specified)

Symbol	Parameter	Test condition	Ratings			Unit
			Min	Typ.	Max	
V_{BR}, V_R	Breakdown voltage, blocking voltage	$I_R=100\mu A$	600	-	-	V
V_F	Forward voltage	$I_F=8A$		$T_J=25^\circ C$	1.53	V
				$T_J=125^\circ C$	1.3	V

I _R	Reverse leakage current	V _R =V _{RRM}	T _J =25℃	-	-	2	μA	
			T _J =125℃	-	-	50	μA	
C _J	Junction Capacitance	V _R =600V		-	15	-	pF	
T _{rr}	Reverse recovery time	I _F =1A, I _R =1A, I _{RR} =0.5A		-	-	20	ns	
			T _J =25℃	-	30	-	ns	
			T _J =125℃	-	50	-	ns	
I _{RRM}	Peak recovery current	I _F =10A, dI _F /dt = 500A/μA, V _R =400V	T _J =25℃	-	4.0	-	A	
			T _J =125℃	-	8.0	-		
Q _{rr}	Reverse recovery charge		T _J =25℃	-	75	-	nC	
			T _J =125℃	-	250	-		
R _{th(j-A)}	Thermal resistance		-		-	-	2.0	℃/W

Typical Performance Curves





Package Dimensions

